ABSTRACT OF THE DISCLOSURE

A semiconductor laser (22) with a semiconductor substrate (11), a laser layer (13) arranged on the semiconductor substrate, a waveguide ridge (15) arranged at a distance from the laser layer, and a strip-shaped lattice structure (23) arranged in parallel to the laser layer is disclosed. The lattice structure (23) includes two structural regions (24, 25) which are arranged on both sides of the waveguide ridge (15) and are formed at a distance from the laser layer (13) above the laser layer (13). A process for the production of such a semiconductor laser is also disclosed.

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